

REMARKS

Applicants have canceled claims 1-709, without prejudice.

Applicants have added new claims 710-908.

New claims 710-908 are identical to claims 1-199 of U.S. Patent Application Serial No. 10/112,578, filed March 29, 2002, and published on November 28, 2002 as U.S. Patent Application Publication No. 2002/0175408, with minor exceptions as noted below.

New claims 710-908 are also identical to claims 1-199 of U.S. Patent Application Serial No. 10/112,698, filed March 29, 2002, and published on November 21, 2002 as U.S. Patent Application Publication No. 2002/0172820, with minor exceptions as noted below.

Applicants note that claims 1-199 of Serial No. 10/112,578 and claims 1-199 of Serial No. 10/112,698 are substantially identical. Differences between these applications are noted below.

Applicants have added paragraph breaks and corrected spacing errors in the claims copied from Serial No. 10/112,578 and Serial No. 10/112,698, solely for legibility purposes. These amendments do not change the scope of the claims.

Applicants have changed "claim" to "claims" in the multiply dependent claims from Serial No. 10/112,578 and Serial No. 10/112,698.

Support for claim 710 can be found on at least page 19, lines 16-20; page 31, lines 25-27; page 43, lines 20-23; and Fig. 1.

Support for claim 711 can be found on at least page 19, lines 16-20; page 31, lines 25-27; page 43, lines 24-26; page 57, lines 1-2; and Fig. 1. A monodisperse distribution of lengths is inherent from descriptions in the specification where nanowires having a single length is discussed.

Support for claim 712 can be found on at least page 9, lines 6-7; page 31, lines 25-27; page 37, lines 6-9; page 58, lines 21-24; page 72, lines 1-4; page 72, lines 29-30; and page 119, lines 16-17.

Support for claim 713 can be found on at least page 31, lines 25-27; and page 116, line 21 to page 117, line 2. Something that varies as a function of radius inherently varies as a function of diameter.

Support for claim 714 can be found on at least page 31, lines 25-27; and page 116, line 21 to page 117, line 2. Applicants have altered the claim, with respect to Serial No. 10/112,578 and

Serial No. 10/112,698, to recite “said at least one electronic property” instead of “said at electronic property.”

Support for claim 715 can be found on at least page 18, lines 3-4; page 19, lines 16-20; page 31, lines 25-27; and Fig. 1. A single crystal is inherently substantially crystalline.

Support for claim 716 can be found on at least page 18, lines 4-6.

Support for claim 717 can be found on at least page 18, lines 25-30; and page 30, lines 6-7. Support for a group II-IV semiconductor, in view of at least page 18, lines 25-30, is inherent in the description “alloys of different groups of semiconductors may also be possible.”

Support for claim 718 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 719 can be found on at least page 18, lines 3-4; page 19, lines 16-20; page 31, lines 25-27; and Fig. 1. A single crystal is inherently substantially crystalline.

Support for claim 720 can be found on at least page 112, lines 7-10.

Support for claim 721 can be found on at least page 19, lines 16-20; page 20, line 20; page 31, lines 25-27; and Fig. 1.

Support for claim 722 can be found on at least page 18, lines 4-6.

Support for claim 723 can be found on at least page 18, lines 25-30; and page 30, lines 6-7. Support for a group II-IV semiconductor, in view of at least page 18, lines 25-30, is inherent in the description “alloys of different groups of semiconductors may also be possible.”

Support for claim 724 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 725 can be found on at least page 18, lines 4-6; page 19, lines 16-20; page 20, line 20; page 31, lines 25-27; and Fig. 1.

Support for claim 726 can be found on at least page 18, lines 25-30; and page 30, lines 6-7. Support for a group II-IV semiconductor, in view of at least page 18, lines 25-30, is inherent in the description “alloys of different groups of semiconductors may also be possible.”

Support for claim 727 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 728 can be found on at least page 18, lines 3-4; page 19, lines 16-20; page 31, lines 25-27; page 33, lines 28-32; and Fig. 1. A single crystal is inherently substantially crystalline.

Support for claim 729 can be found on at least page 112, lines 7-10.

Support for claim 730 can be found on at least page 18, lines 3-4; page 19, lines 16-20; page 31, lines 25-27; page 33, lines 28-32; page 112, lines 7-10; and Fig. 1. A single crystal is inherently substantially crystalline.

Support for claim 731 can be found on at least page 20, line 20.

Support for claim 732 can be found on at least page 18, lines 4-6.

Support for claim 733 can be found on at least page 18, lines 25-30; and page 30, lines 6-7. Support for a group II-IV semiconductor, in view of at least page 18, lines 25-30, is inherent in the description “alloys of different groups of semiconductors may also be possible.”

Support for claim 734 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 735 can be found on at least page 19, lines 16-20; page 20, line 20; page 31, lines 25-27; page 33, lines 28-32; and Fig. 1.

Support for claim 736 can be found on at least page 18, lines 4-6.

Support for claim 737 can be found on at least page 18, lines 25-30; and page 30, lines 6-7. Support for a group II-IV semiconductor, in view of at least page 18, lines 25-30, is inherent in the description “alloys of different groups of semiconductors may also be possible.”

Support for claim 738 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 739 can be found on at least page 18, lines 4-6; page 19, lines 16-20; page 20, line 20; page 31, lines 25-27; page 33, lines 28-32; and Fig. 1.

Support for claim 740 can be found on at least page 18, lines 25-30; and page 30, lines 6-7. Support for a group II-IV semiconductor, in view of at least page 18, lines 25-30, is inherent in the description “alloys of different groups of semiconductors may also be possible.”

Support for claim 741 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 742 can be found on at least page 18, lines 3-4; page 19, lines 16-20; page 31, lines 25-27; page 33, line 28 to page 34, line 7; and Fig. 1. A single crystal is inherently substantially crystalline. It is inherent that, in a gradual transition between a first composition and a second composition in a nanowire, there will be a point in the overlap zone where the ratio between the first composition and the second composition is 99:1.

Support for claim 743 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially crystalline.

Support for claim 744 can be found on at least page 18, lines 3-4; page 19, lines 16-20; page 31, lines 25-27; page 33, line 28 to page 34, line 7; and Fig. 1. A single crystal is inherently substantially crystalline. It is inherent that, in a gradual transition between a first composition and a second composition in a nanowire, there will be a point in the overlap zone where the ratio between the first composition and the second composition is 99:1.

Support for claim 745 can be found on at least page 20, line 20.

Support for claim 746 can be found on at least page 18, lines 4-6.

Support for claim 747 can be found on at least page 18, lines 25-30; and page 30, lines 6-7. Support for a group II-IV semiconductor, in view of at least page 18, lines 25-30, is inherent in the description “alloys of different groups of semiconductors may also be possible.” It is noted that claim 38 of Serial No. 10/112,578 recites “a group II-V semiconductor,” while claim 38 of Serial No. 10/112,698 recites “a group III-V semiconductor.” It is believed that “a group II-V semiconductor,” is a typographical error in Serial No. 10/112,578.

Support for claim 748 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 749 can be found on at least page 19, lines 16-20; page 20, line 20; page 31, lines 25-27; page 33, line 28 to page 34, line 7; and Fig. 1. It is inherent that, in a gradual transition between a first composition and a second composition in a nanowire, there will be a point in the overlap zone where the ratio between the first composition and the second composition is 99:1.

Support for claim 750 can be found on at least page 18, lines 4-6.

Support for claim 751 can be found on at least page 18, lines 25-30; and page 30, lines 6-7. Support for a group II-IV semiconductor, in view of at least page 18, lines 25-30, is inherent in the description “alloys of different groups of semiconductors may also be possible.”

Support for claim 752 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 753 can be found on at least page 18, lines 4-6; page 19, lines 16-20; page 31, lines 25-27; page 33, lines 28-32; and Fig. 1.

Support for claim 754 can be found on at least page 18, lines 25-30; and page 30, lines 6-7. Support for a group II-IV semiconductor, in view of at least page 18, lines 25-30, is inherent in the description “alloys of different groups of semiconductors may also be possible.” It is noted that claim 45 of Serial No. 10/112,578 recites “a group II-V semiconductor,” while claim 45 of Serial No. 10/112,698 recites “a group III-V semiconductor.” It is believed that “a group II-V semiconductor,” is a typographical error in Serial No. 10/112,578.

Support for claim 755 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 756 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially crystalline.

Support for claim 757 can be found on at least page 31, lines 25-27.

Support for claim 758 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially crystalline.

Support for claim 759 can be found on at least page 33, line 28 to page 34, line 1.

Support for claim 760 can be found on at least page 34, lines 12-13.

Support for claim 761 can be found on at least page 32, line 16.

Support for claim 762 can be found on at least page 18, lines 3-7.

Support for claim 763 can be found on at least page 33, line 31 to page 34, line 7. It is inherent that, in a gradual transition between a first composition and a second composition in a nanowire, there will be a point in the overlap zone where the ratio between the first composition and the second composition is 99:1.

Support for claim 764 can be found on at least page 33, lines 28-32.

Support for claim 765 can be found on at least page 34, lines 12-13.

Support for claim 766 can be found on at least page 32, line 16.

Support for claim 767 can be found on at least page 18, lines 3-7.

Support for claim 768 can be found on at least page 33, line 31 to page 34, line 7. It is inherent that, in a gradual transition between a first composition and a second composition in a nanowire, there will be a point in the overlap zone where the ratio between the first composition and the second composition is 99:1.

Support for claim 769 can be found on at least page 20, line 20.

Support for claim 770 can be found on at least page 18, lines 4-6.

Support for claim 771 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 772 can be found on at least page 19, lines 16-23.

Support for claim 773 can be found on at least page 19, lines 16-20; page 43, lines 27-29; and Fig. 1.

Support for claim 774 can be found on at least page 19, lines 16-20; and Fig. 1.

Support for claim 775 can be found on at least page 31, lines 27-28.

Support for claim 776 can be found on at least page 132, line 31 to page 133, line 1.

Support for claim 777 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially monocrystalline.

Support for claim 778 can be found on at least page 18, lines 3-4; and page 32, line 16. A single crystal is inherently substantially monocrystalline.

Support for claim 779 can be found on at least page 32, line 7.

Support for claim 780 can be found on at least page 49, lines 23-25.

Support for claim 781 can be found on at least page 32, line 8.

Support for claim 782 can be found on at least page 49, lines 23-25.

Support for claim 783 can be found on at least page 32, lines 8-9.

Support for claim 784 can be found on at least page 49, lines 23-25.

Support for claim 785 can be found on at least page 39, lines 26-28.

Support for claim 786 can be found on at least page 18, lines 22-26.

Support for claim 787 can be found on at least page 36, lines 9-13. A polymer shell that surrounds a nanowire inherently embeds the nanowire.

Support for claim 788 can be found on at least page 33, lines 1-3.

Support for claim 789 can be found on at least page 79, lines 21-23.

Support for claim 790 can be found on at least page 128, lines 15-16.

Support for claim 791 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially monocrystalline.

Support for claim 792 can be found on at least page 18, line 12; page 38, lines 9-11; page 49, lines 21-25; page 50, line 9; page 50, lines 21-23; page 53, lines 29-31; page 54, lines 2-4; page 61, lines 9-12; page 83, line 21; page 109, line 2. Applicants have deleted phonon band gap devices, thermoelectric devices, nanoelectromechanical actuators, infrared detectors, infrared detectors, optical modulators, optical couplers and optical switches, and a stray “)” with respect to claim 83 of Serial No. 10/112,578 and claim 83 of Serial No. 10/112,698.

Support for claim 793 can be found on at least page 56, lines 3-6.

Support for claim 794 can be found on at least page 60, lines 1-2.

Support for claim 795 can be found on at least page 60, lines 1-2.

Support for claim 796 can be found on at least page 106, lines 8-10.

Support for claim 797 can be found on at least page 56, lines 18-19.

Support for claim 798 can be found on at least page 51, lines 10-14. Applicants have also changed the claim from “recited in 88” to “recited in claim 797.”

Support for claim 799 can be found on at least page 55, lines 11-13.

Support for claim 800 can be found on at least page 55, lines 11-13.

Support for claim 801 can be found on at least page 106, lines 27-30.

Support for claim 802 can be found on at least pages 106, lines 11-14; and Fig. 60b.

Support for claim 803 can be found on at least Fig. 27b.

Support for claim 804 can be found on at least page 18, lines 6-8; and page 23, lines 10-11.

Support for claim 805 can be found on at least page 57, lines 3-5.

Support for claim 806 can be found on at least page 57, lines 1-8. A memory array having multiple planes, with each plane having 1000 nanowires, has more than 1000 nanowires.

Support for claim 807 can be found on at least page 56, lines 7-8.

Support for claim 808 can be found on at least page 56, lines 7-8.

Support for claim 809 can be found on at least page 51, lines 9-10.

Support for claim 810 can be found on at least page 29, lines 17-25.

Support for claim 811 can be found on at least page 46, lines 8-10.

Support for claim 812 can be found on at least page 25, line 22; page 46, lines 8-10; and page 110, lines 5-6. Applicants have deleted a glass and a gel with respect to claim 103 of Serial No. 10/112,578 and claim 103 of Serial No. 10/112,698.

Support for claim 813 can be found on at least page 36, lines 9-13. A polymer shell that surrounds a nanowire inherently embeds the nanowire.

Support for claim 814 can be found on at least page 56, lines 18-19.

Support for claim 815 can be found on at least page 51, lines 10-14.

Support for claim 816 can be found on at least page 55, lines 11-13.

Support for claim 817 can be found on at least page 55, lines 11-13.

Support for claim 818 can be found on at least page 106, lines 27-30.

Support for claim 819 can be found on at least pages 106, lines 11-14; and Fig. 60b.

Support for claim 820 can be found on at least Fig. 27b.

Support for claim 821 can be found on at least page 42, lines 4-6.

Support for claim 822 can be found on at least page 42, lines 4-6.

Support for claim 823 can be found on at least page 19, lines 16-20; page 33, lines 1-3; and Fig. 1.

Support for claim 824 can be found on at least Fig. 1.

Support for claim 825 can be found on at least page 33, lines 28-32.

Support for claim 826 can be found on at least page 33, line 31 to page 34, line 7. It is inherent that, in a gradual transition between a first composition and a second composition in a nanowire, there will be a point in the overlap zone where the ratio between the first composition and the second composition is 99:1.

Support for claim 827 can be found on at least page 31, lines 27-28.

Support for claim 828 can be found on at least page 32, lines 31-32.

Support for claim 829 can be found on at least page 132, line 31 to page 133, line 1.

Support for claim 830 can be found on at least page 128, lines 15-16.

Support for claim 831 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially monocrystalline.

Support for claim 832 can be found on at least page 20, line 20.

Support for claim 833 can be found on at least page 18, lines 4-6.

Support for claim 834 can be found on at least page 34, line 32 to page 35, line 4; and page 41, lines 15-18. Each segment defining a p/n junction inherently has different electrical characteristics.

Support for claim 835 can be found on at least page 19, lines 16-23.

Support for claim 836 can be found on at least page 32, line 7.

Support for claim 837 can be found on at least page 32, line 8.

Support for claim 838 can be found on at least page 32, lines 8-9.

Support for claim 839 can be found on at least page 32, lines 7-32. A nanowire having a p-n junction is inherent from the description.

Support for claim 840 can be found on at least page 32, lines 7-32. A nanowire having a n-p junction is inherent from the description.

Support for claim 841 can be found on at least page 32, lines 7-32. A nanowire having a p-i-n junction is inherent from the description.

Support for claim 842 can be found on at least page 32, lines 7-32. A nanowire having a p-i-p junction is inherent from the description.

Support for claim 843 can be found on at least page 49, lines 23-25.

Support for claim 844 can be found on at least page 39, lines 26-28.

Support for claim 845 can be found on at least page 18, lines 22-26.

Support for claim 846 can be found on at least page 36, lines 9-13. A polymer shell that surrounds a nanowire inherently embeds the nanowire.

Support for claim 847 can be found on at least page 33, lines 1-3.

Support for claim 848 can be found on at least page 79, lines 21-23.

Support for claim 849 can be found on at least page 128, lines 15-16.

Support for claim 850 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially monocrystalline.

Support for claim 851 can be found on at least page 18, line 12; page 38, lines 9-11; page 49, lines 21-25; page 50, line 9; page 50, lines 21-23; page 53, lines 29-31; page 54, lines 2-4;

page 61, lines 9-12; page 83, line 21; page 109, line 2. Applicants have deleted phonon band gap devices, thermoelectric devices, nanoelectromechanical actuators, infrared detectors, infrared detectors, optical modulators, optical couplers and optical switches, and a stray “)” with respect to claim 142 of Serial No. 10/112,578 and claim 142 of Serial No. 10/112,698.

Support for claim 852 can be found on at least page 56, lines 3-6.

Support for claim 853 can be found on at least page 19, lines 16-20; page 41, lines 19-25; and Fig. 1.

Support for claim 854 can be found on at least page 41, lines 19-25. Different liquid alloys are inherently formed from different gas reactants.

Support for claim 855 can be found on at least page 41, lines 19-20

Support for claim 856 can be found on at least page 43, lines 6-8.

Support for claim 857 can be found on at least page 41, lines 19-20; and page 43, lines 6-8.

Support for claim 858 can be found on at least page 42, line 31 to page 43, line 2. Applicants have also changed the claim from “recited in 144” to “recited in claim 853.”

Support for claim 859 can be found on at least page 43, lines 20-26. Applicants have also changed the claim from “recited in 149” to “recited in claim 858.”

Support for claim 860 can be found on at least page 19, lines 16-20; page 41, lines 19-25; page 42, lines 9-11; and Fig. 1.

Support for claim 861 can be found on at least page 41, lines 19-25.

Support for claim 862 can be found on at least page 42, line 31 to page 43, line 2.

Support for claim 863 can be found on at least page 43, lines 20-26.

Support for claim 864 can be found on at least page 19, lines 16-20; page 33, lines 1-3; page 41, lines 19-25; page 42, lines 9-11; and Fig. 1.

Support for claim 865 can be found on at least page 19, lines 16-20; page 33, lines 1-3; page 41, lines 19-25; and Fig. 1.

Support for claim 866 can be found on at least page 32, lines 19-23; and page 41, line 30 to page 42, line 1.

Support for claim 867 can be found on at least page 41, lines 19-25.

Support for claim 868 can be found on at least page 41, lines 19-20; and page 43, lines 6-8.

Support for claim 869 can be found on at least page 19, lines 16-20; page 41, lines 19-25; page 43, lines 6-8; and Fig. 1. Applicants have also deleted an extra “and” with respect to claim 160 of Serial No. 10/112,578 and claim 160 of Serial No. 10/112,698.

Support for claim 870 can be found on at least page 19, lines 16-20; page 41, lines 19-25; page 43, lines 6-8; and Fig. 1. Different liquid alloys are inherently formed from different gas reactants.

Support for claim 871 can be found on at least page 41, lines 19-25. Different liquid alloys are inherently formed from different gas reactants.

Support for claim 872 can be found on at least page 19, lines 16-20; page 41, lines 19-25; page 110, line 31 to page 111, line 8; and Fig. 1. Applicants have also added a missing “;” with respect to Serial No. 10/112,578 and Serial No. 10/112,698.

Support for claim 873 can be found on at least page 42, line 4.

Support for claim 874 can be found on at least page 42, lines 2-4.

Support for claim 875 can be found on at least page 76, lines 25-28.

Support for claim 876 can be found on at least page 41, lines 20-23; and page 42, lines 2-4.

Support for claim 877 can be found on at least page 77, line 32 to page 78, line 2.

Support for claim 878 can be found on at least page 43, lines 4-5. Applicants have deleted SiCl_4 with respect to claim 169 of Serial No. 10/112,578 and claim 169 of Serial No. 10/112,698.

Support for claim 879 can be found on at least page 19, lines 16-20; page 41, lines 19-25; page 43, lines 4-5; page 110, line 31 to page 111, line 8; page 133, lines 17-26; Example 3; Example 4; and Fig. 1. Applicants have deleted SiCl_4 with respect to claim 170 of Serial No. 10/112,578 and claim 170 of Serial No. 10/112,698.

Support for claim 880 can be found on at least page 80, lines 3-12; and page 83, lines 27-28.

Support for claim 881 can be found on at least page 42, line 4.

Support for claim 882 can be found on at least page 76, lines 25-28.

Support for claim 883 can be found on at least page 41, lines 20-23.

Support for claim 884 can be found on at least Fig. 1.

Support for claim 885 can be found on at least page 33, lines 28-32.

Support for claim 886 can be found on at least page 33, line 31 to page 34, line 7. It is inherent that, in a gradual transition between a first composition and a second composition in a nanowire, there will be a point in the overlap zone where the ratio between the first composition and the second composition is 99:1.

Support for claim 887 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially crystalline.

Support for claim 888 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially monocrystalline.

Support for claim 889 can be found on at least page 20, line 20.

Support for claim 890 can be found on at least page 41, lines 8-9.

Support for claim 891 can be found on at least page 19, lines 16-23.

Support for claim 892 can be found on at least page 31, lines 27-28.

Support for claim 893 can be found on at least page 132, line 31 to page 133, line 1.

Support for claim 894 can be found on at least page 32, line 7.

Support for claim 895 can be found on at least page 49, lines 23-25.

Support for claim 896 can be found on at least page 32, line 8.

Support for claim 897 can be found on at least page 49, lines 23-25.

Support for claim 898 can be found on at least page 32, lines 8-9.

Support for claim 899 can be found on at least page 49, lines 23-25.

Support for claim 900 can be found on at least page 39, lines 26-28.

Support for claim 901 can be found on at least page 18, lines 22-26.

Support for claim 902 can be found on at least page 36, lines 9-13. A polymer shell that surrounds a nanowire inherently embeds the nanowire.

Support for claim 903 can be found on at least page 33, lines 1-3.

Support for claim 904 can be found on at least page 79, lines 21-23.

Support for claim 905 can be found on at least page 128, lines 15-16.

Support for claim 906 can be found on at least page 18, lines 3-4. A single crystal is inherently substantially monocrystalline.

Support for claim 907 can be found on at least page 18, line 12; page 38, lines 9-11; page 49, lines 21-25; page 50, line 9; page 50, lines 21-23; page 53, lines 29-31; page 54, lines 2-4; page 61, lines 9-12; page 83, line 21; page 109, line 2. Applicants have deleted phonon band gap

devices, thermoelectric devices, nanoelectromechanical actuators, infrared detectors, infrared detectors, optical modulators, optical couplers and optical switches, and a stray “)” with respect to claim 198 of Serial No. 10/112,578 and claim 198 of Serial No. 10/112,698.

Support for claim 908 can be found on at least page 56, lines 3-6.

CONCLUSION

New claims 710-908 are identical to claims 1-199 of U.S. Patent Application Serial No. 10/112,578, filed March 29, 2002, and published on November 28, 2002 as U.S. Patent Application Publication No. 2002/0175408, with minor exceptions as noted below.

New claims 710-908 are also identical to claims 1-199 of U.S. Patent Application Serial No. 10/112,698, filed March 29, 2002, and published on November 21, 2002 as U.S. Patent Application Publication No. 2002/0172820, with minor exceptions as noted below.

If this response is not considered timely filed and if a request for an extension of time is otherwise absent, Applicant hereby requests any necessary extension of time. Please charge any fee deficiency to Deposit Account No. 23/2825.

Respectfully submitted,
Lieber, et al., Applicant

By: 

Timothy J. Oyer, Reg. No. 36,628
Tani Chen, Reg. No. 52,728
Wolf, Greenfield & Sacks, P.C.
600 Atlantic Avenue
Boston, Massachusetts 02210-2211
Telephone: (617) 720-3500

Date: November 21, 2003